## NSN 5962-01-203-8634

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Body Length:	
0.840 inches	
Body Width:	
Between 0.220 inche	es and 0.310 inches
Body Height:	
0.185 inches	
Maximum Power D	ssipation Rating:
794.0 milliwatts	
Operating Tempura	iture Range:
-55.0/+125.0 degree	s celsius
Storage Tempuratu	ire Range:
-65.0/+150.0 degree	s celsius
Features Provided:	
3-state output and b	polar and programmed and schottky and w/active pull-up
Inclosure Material:	
Ceramic or glass or	metal
Inclosure Configur	ation:
Dual-in-line	
Output Logic Form	:
Transistor-transistor	logic
Input Circuit Patter	n:
10 input	
Case Outline Sourc	e And Designator:
D-2 mil-m-38510	
Terminal Surface T	reatment:
Solder	
Voltage Rating And	I Type Per Characteristic:
-0.5 volts power sou	Irce and 7.0 volts power source
Time Rating Per Ch	acteristic:
85.00 nanoseconds	propagation delay time, low to high level output and 85.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Ty	be:
Prom	
Test Data Docume	nt:
96906-mil-std-883 st	andard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And	Quantity:
16 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	
 Demilitarization:	
Yes - demil/mli	

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